

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

5 a switching thin film transistor which operates by receiving
an element driving thin film transistor provided between a
driving power supply and an element to be driven, for controlling
the power supplied from said driving power supply to said element
to be driven based on a data signal supplied from said switching
thin film transistor; characterized in that

10 a compensation thin film transistor having an opposite
conductive characteristic with respect to said element driving thin
film transistor is provided between said driving power supply and
said element driving thin film transistor.

15 2. A semiconductor device according to claim 1, wherein a gate and
either a source or a drain of said compensation thin film transistor
are connected, and said compensation thin film transistor is
connected between said driving power supply and said element driving
20 thin film transistor.

25 3. A semiconductor device according to claim 1, wherein said
element driving thin film transistor comprises a plurality of thin
film transistors connected to each other in parallel.

4. A semiconductor device according to claim 3, wherein said
compensation thin film transistor is a diode connected transistor
connected between said driving power supply and said element driving
thin film transistor.

5. A semiconductor device according to claim 1, wherein
said element driving thin film transistor comprises a
plurality of thin film transistors connected between said driving
power supply and said element to be driven and in parallel to each
5 other; and

said compensation thin film transistor is respectively
provided between said plurality of thin film transistors connected
in parallel and said driving power supply.

10 6. A semiconductor device according to claim 5, wherein said
compensation thin film transistor is a diode connected transistor
connected between said driving power supply and said element driving
thin film transistor.

15 7. A semiconductor device according to claim 1, wherein said
element to be driven is an electroluminescence element which
includes an emissive layer between a first electrode and a second
electrode.

20 8. A semiconductor device according to claim 6, wherein said
electroluminescence element is an organic electroluminescence
element which employs an organic compound in an emissive layer.

25 9. A semiconductor device according to claim 1, wherein said
semiconductor device is used for an active matrix type display
device wherein each of the pixels arranged in a matrix form comprises
said switching thin film transistor, said element driving thin film
transistor, said compensation thin film transistor, and said
element to be driven as a display element.

10. A semiconductor device according to claim 1, wherein said element driving thin film transistor and said compensation thin film transistor are placed so that the channel length direction of said thin film transistors is along the extension direction of the data line for supplying said data signal to said switching thin film transistor.

11. A semiconductor device according to claim 1, wherein the channel length direction of said element driving thin film transistor does not coincide with the channel length direction of said switching thin film transistor.

12. A semiconductor device according to claim 1, wherein said element driving thin film transistor is formed so that its channel length direction is along the scan direction of a line pulse laser for annealing the channel region of the transistor.

13. A semiconductor device according to claim 12, wherein a gate and either a source or a drain of said compensation thin film transistor are connected, and said compensation thin film transistor is connected between said driving power supply and said element driving thin film transistor.